This GIDEP PCN is to announce specifications change with the datasheet parameters for the following International Rectifier Part No. Note that this change is related to part specification only, and not due to a die physical change.

**IRHNJ7130 [2N7380U3]**

100V, N-Channel TID Hardened MOSFET in a SM-0.5 package

**ABSOLUTE MAXIMUM RATINGS**

$I_{DM}$ [Pulsed Drain Current], change max rating from 58A to 57.6A.
Linear Derating Factor, change from 1.2 W/°C to 0.6 W/°C.

**ELECTRICAL CHARACTERISTICS @ $T_j = 25^\circ$C**

$t_f$ [Fall Time], change max limit from 60ns to 30ns.

**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS**

$I_{SM}$ [Pulse Source Current (Body Diode)], change max limit from 58A to 57.6A.

**RADIATION CHARACTERISTICS CHANGE** Table 1 Electrical Characteristics @ $T_j = 25^\circ$C, Post Total Dose Irradiation

$BV_{DSS}$ [Drain-to-Source Breakdown Voltage], change min limit at 300K-1000K Rads(Si) from 60V to 100V.
$Idss$ [Zero Gate Voltage Drain Current], change max limit at 300K-1000K Rads(Si) from 25μA to 50μA.
$R_{DS(ON)}$ (Static Drain-to-Source On-State Resistance (TO-3)), change max limit at 100K Rads(Si) from 0.19Ω to 0.18Ω.
$R_{DS(ON)}$ (Static Drain-to-Source On-State Resistance (TO-3)), change max limit at 300K-1000K Rads(Si) from 0.25Ω to 0.24Ω.

Reference Datasheet PD-93820